

Tadas Malinauskas

List of Publications by Year in descending order

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papers

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57
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citing authors

#	ARTICLE	IF	CITATIONS
1	MOVPE Growth of GaN via Graphene Layers on GaN/Sapphire Templates. <i>Nanomaterials</i> , 2022, 12, 785.	1.9	10
2	Hierarchical Carbon Nanocone-Silica Metamaterials: Implications for White Light Photoluminescence. <i>ACS Applied Nano Materials</i> , 2022, 5, 4787-4800.	2.4	6
3	The Crystalline Structure of Thin Bismuth Layers Grown on Silicon (111) Substrates. <i>Materials</i> , 2022, 15, 4847.	1.3	1
4	The importance of nucleation layer for the GaN N-face purity on the annealed Al ₂ O ₃ layers deposited by atomic layer deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2022, 284, 115850.	1.7	0
5	Remote epitaxy of GaN via graphene on GaN/sapphire templates. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 205103.	1.3	26
6	Extension of spectral sensitivity of GeSn IR photodiode after laser annealing. <i>Applied Surface Science</i> , 2021, 555, 149711.	3.1	10
7	Temperature and spatial dependence of carrier lifetime and luminescence intensity in Ge _{0.95} Sn _{0.05} layer. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021, 270, 115204.	1.7	3
8	Study of the electrical characteristics of CdZnTe Schottky diodes. <i>Materials Science in Semiconductor Processing</i> , 2020, 105, 104705.	1.9	4
9	Temperature dependent carrier lifetime, diffusion coefficient, and diffusion length in Ge _{0.95} Sn _{0.05} epilayer. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	7
10	A comparative study on atomic layer deposited oxide film morphology and their electrical breakdown. <i>Surface and Coatings Technology</i> , 2020, 399, 126123.	2.2	8
11	Direct-indirect GeSn band structure formation by laser Radiation: The enhancement of Sn solubility in Ge. <i>Optics and Laser Technology</i> , 2020, 128, 106200.	2.2	11
12	Highly efficient nanocrystalline Cs _x MA _{1-x} PbBr _x perovskite layers for white light generation. <i>Nanotechnology</i> , 2019, 30, 345702.	1.3	2
13	Improvement of luminescence properties of InN by optimization of multi-step deposition on sapphire. <i>Thin Solid Films</i> , 2019, 680, 89-93.	0.8	1
14	The detrimental effect of AlGaN barrier quality on carrier dynamics in AlGaN/GaN interface. <i>Scientific Reports</i> , 2019, 9, 17346.	1.6	6
15	Engineering of InN epilayers by repeated deposition of ultrathin layers in pulsed MOCVD growth. <i>Applied Surface Science</i> , 2018, 427, 1027-1032.	3.1	25
16	Significant Carrier Extraction Enhancement at the Interface of an InN/p-GaN Heterojunction under Reverse Bias Voltage. <i>Nanomaterials</i> , 2018, 8, 1039.	1.9	6
17	Growth conditions of semi and non-polar GaN on Si with Er ₂ O ₃ buffer layer. <i>Journal of Alloys and Compounds</i> , 2017, 725, 739-743.	2.8	4
18	Study of recombination characteristics in MOCVD grown GaN epi-layers on Si. <i>Semiconductor Science and Technology</i> , 2017, 32, 125014.	1.0	5

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19	Facet analysis of truncated pyramid semi-polar GaN grown on Si(100) with rare-earth oxide interlayer. Journal of Applied Physics, 2016, 120, 105301.	1.1	3
20	Influence of metalorganic precursors flow interruption timing on green InGaN multiple quantum wells. Journal Physics D: Applied Physics, 2016, 49, 505101.	1.3	7
21	Solar water splitting: Efficiency discussion. International Journal of Hydrogen Energy, 2016, 41, 11941-11948.	3.8	37
22	Optical and structural properties of B GaN layers grown on different substrates. Journal Physics D: Applied Physics, 2015, 48, 465307.	1.3	24
23	Carrier dynamics in blue and green emitting InGaN MQWs. Physica Status Solidi (B): Basic Research, 2015, 252, 977-982.	0.7	11
24	Growth of InN and In-Rich InGaN Layers on GaN Templates by Pulsed Metalorganic Chemical Vapor Deposition. Journal of Electronic Materials, 2015, 44, 188-193.	1.0	16
25	A systematic study of light extraction efficiency enhancement depended on sapphire flipside surface patterning by femtosecond laser. Journal Physics D: Applied Physics, 2015, 48, 285104.	1.3	10
26	Growth of B GaN epitaxial layers using close-coupled showerhead MOCVD. Physica Status Solidi (B): Basic Research, 2015, 252, 1138-1141.	0.7	16
27	Defect study of GaN based LED structure by electron beam induced current. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 734-737.	0.8	0
28	In _x Ga _{1-x} N performance as a band-gap-tunable photo-electrode in acidic and basic solutions. Solar Energy Materials and Solar Cells, 2014, 130, 36-41.	3.0	24
29	Relationships Between Strain and Recombination in Intermediate Growth Stages of GaN. Journal of Electronic Materials, 2014, 43, 2667-2675.	1.0	1
30	Peculiarities of photoluminescence efficiency dependence on excitation intensity in GaN/Al ₂ O ₃ epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 511-514.	0.8	1
31	Study of carrier recombination transient characteristics in MOCVD grown GaN dependent on layer thickness. AIP Advances, 2013, 3, 112128.	0.6	4
32	Impact of Diffusivity to Carrier Recombination Rate in Nitride Semiconductors: From Bulk GaN to (In,Ga)N Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 08JK01.	0.8	9
33	Holographic study of ultrafast optical excitation in GaN film induced by nonlinear propagation of light. Optics Letters, 2012, 37, 4916.	1.7	5
34	Nonlinear Optical Techniques for Characterization of Wide Bandgap Semiconductor Electronic Properties: III-nitrides, SiC, and Diamonds. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	1
35	Suppression of surface recombination in surface plasmon coupling with an InGaN/GaN multiple quantum well sample. Optics Express, 2011, 19, 18893.	1.7	9
36	Direct study of nonlinear carrier recombination in InGaN quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2381-2383.	0.8	6

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37	High-excitation luminescence properties of m-plane GaN grown on LiAlO ₂ substrates. <i>Journal of Crystal Growth</i> , 2011, 329, 33-38.	0.7	2
38	Carrier dynamics in InGaN/GaN multiple quantum wells based on different polishing processes of sapphire substrate. <i>Thin Solid Films</i> , 2010, 518, 7291-7294.	0.8	6
39	Carrier dynamics in coalescence overgrowth of GaN nanocolumns. <i>Thin Solid Films</i> , 2010, 519, 863-867.	0.8	15
40	Layer thickness dependent carrier recombination rate in HVPE GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1703-1706.	0.7	11
41	Dynamics of free carrier absorption in InN layers. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	11
42	Carrier dynamics in Fe-doped GaN epilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S723-S726.	0.8	3
43	Nonlinear carrier recombination and transport features in highly excited InN layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S735-S738.	0.8	6
44	Diffusion and recombination of degenerate carrier plasma in GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S743-S746.	0.8	19
45	Recombination of free and bound excitons in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1723-1740.	0.7	100
46	Heterodyne detection scheme for light-induced transient grating experiment. <i>Optics Communications</i> , 2008, 281, 6061-6064.	1.0	2
47	Advantages of the time-resolved four-wave mixing technique for studies of non-equilibrium carrier dynamics in bulk semiconductors and structures. <i>Optical Materials</i> , 2008, 30, 780-782.	1.7	2
48	Optical evaluation of carrier lifetime and diffusion length in synthetic diamonds. <i>Diamond and Related Materials</i> , 2008, 17, 1212-1215.	1.8	44
49	All-optical characterization of carrier lifetimes and diffusion lengths in MOCVD-, ELO-, and HVPE-grown GaN. <i>Journal of Crystal Growth</i> , 2007, 300, 223-227.	0.7	31
50	Photoelectric properties of highly excited GaN:Fe epilayers, grown by modulation- and continuous-doping techniques. <i>Journal of Crystal Growth</i> , 2007, 300, 228-232.	0.7	3
51	Contribution of dislocations to carrier recombination and transport in highly excited ELO and HVPE GaN layers. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1426-1430.	0.7	32
52	The determination of high-density carrier plasma parameters in epitaxial layers, semi-insulating and heavily doped crystals of 4H-SiC by a picosecond four-wave mixing technique. <i>Semiconductor Science and Technology</i> , 2006, 21, 952-958.	1.0	29
53	Optical monitoring of nonequilibrium carrier lifetime in freestanding GaN by time-resolved four-wave mixing and photoluminescence techniques. <i>Applied Physics Letters</i> , 2006, 88, 202109.	1.5	40
54	Application of picosecond four-wave mixing and photoluminescence techniques for investigation of carrier dynamics in bulk crystals and heterostructures of GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1006-1009.	0.8	7

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55	Studies of carrier dynamics in epitaxial heterostructures by nonlinear optical and microwave techniques. <i>Physica Status Solidi A</i> , 2003, 195, 238-242.	1.7	3
56	Determination of free carrier bipolar diffusion coefficient and surface recombination velocity of undoped GaN epilayers. <i>Applied Physics Letters</i> , 2003, 83, 1157-1159.	1.5	68
57	Carrier Diffusivity in Highly Excited Bulk SiC, GaN, and Diamond Crystals by Optical Probes. <i>Materials Science Forum</i> , 0, 717-720, 309-312.	0.3	6